Vishay Siliconix

P-Channel 40 V (D-S), 175 °C MOSFET



PRODUCT SUMMARY			
V _{DS} (V)	-40		
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -10 \text{ V}$	0.0094		
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5 \text{ V}$	0.0145		
I _D (A) ^d	-50		
Configuration	Single		

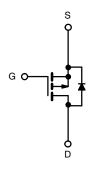
FEATURES

- TrenchFET® power MOSFETs
- 175 °C junction temperature



ROHS COMPLIANT

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



P-Channel MOSFET

ORDERING INFORMATION		
Package	DPAK (TO-252)	
Lead (Pb)-free	SUD50P04-09L-E3	

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	-40	V
Gate-source voltage		V_{GS}	± 20	7 v
Continuous dusin surrent (T. 175 °C)	T _C = 25 °C	I _D	-50 ^d	A
Continuous drain current (T _J = 175 °C)	T _C = 125 °C		-50 ^d	
Pulsed drain current		I _{DM}	-100] ^
Avalanche current		I _{AS}	-50	
Single avalanche energy ^a	L = 0.1 mH	E _{AS}	125	mJ
Power dissipation	T _C = 25 °C	В	136 ^c	W
	T _A = 25 °C	P _D	3 b, c	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-ambient ^b	t ≤ 10 s	R _{thJA}	15	18	
Junction-to-ambient *	Steady state		40	50	°C/W
Junction-to-case	•	R _{thJC}	0.82	1.1	

Notes

- a. Duty cycle $\leq 1\%$
- b. When mounted on 1" square PCB (FR4 material)
- c. See SOA curve for voltage derating
- d. Package limited



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-40	-	-	V
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-1	-	-3	V
Gate-body leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{DS} = -32 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	-1	
Zero gate voltage drain current	I _{DSS}	V _{DS} = -32 V, V _{GS} = 0 V, T _J = 125 °C	-	-	-50	μΑ
		V _{DS} = -32 V, V _{GS} = 0 V, T _J = 175 °C	-	-	-150	
On-state drain current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-50	-	-	Α
		V _{GS} = -10 V, I _D = -24 A	-	0.0075	0.0094	
Drain aguros en etata registance à	В	V _{GS} = -10 V, I _D = -50 A, T _J = 125 °C	-	-	0.0140	0
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = -10 V, I _D = -50 A, T _J = 175 °C	-	-	0.0170	Ω
		$V_{GS} = -4.5 \text{ V}, I_D = -18 \text{ A}$ - 0.0	0.0115	0.0145		
Forward transconductance a	9fs	$V_{DS} = -5 \text{ V}, I_D = -24 \text{ A}$	-	73	-	S
Dynamic ^b						
Input capacitance	C _{iss}		-	4800	-	
Output capacitance	Coss	$V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$	-	700	-	рF
Reverse transfer capacitance	C _{rss}		-	550	-	
Total gate charge ^c	Qg		-	102	150	
Gate-source charge ^c	Q_{gs}	$V_{DS} = -20 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -50 \text{ A}$	-	18.5	-	nC
Gate-drain charge ^c	Q_{gd}		-	27	-	
Turn-on delay time ^c	t _{d(on)}		-	10	15	
Rise time ^c	t _r	V_{DD} = -20 V, R_L = 0.4 Ω	-	60	90	no
Turn-off delay time ^c	t _{d(off)}	$I_D\cong$ -50 A, V_{GEN} = -10 V, R_g = 6 Ω	-	145	220	ns
Fall time ^c	t _f		-	140	220	
Source Drain-Diode Ratings and Ch	aracteristics ^t	P (T _C = 25 °C)				
Continuous current	I _S		-	-	-50	Α
Pulsed current	I _{SM}		-	-	-100	
Forward voltage ^a	V _{SD}	I _F = -50 A, V _{GS} = 0 V	-	-1	-1.5	V
Reverse recovery time	t _{rr}	I _F = -50 A, di/dt = 100 A/μs	_	55	85	ns

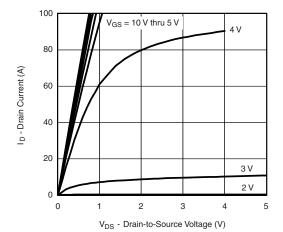
Notes

- a. Pulse test; pulse width $\leq 300 \,\mu\text{s}$, duty cycle $\leq 2\%$
- a. Guaranteed by design, not subject to production testing
- b. Independent of operating temperature

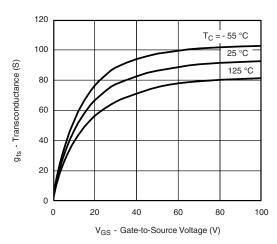
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability



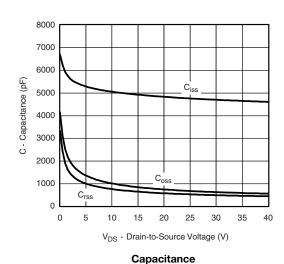
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

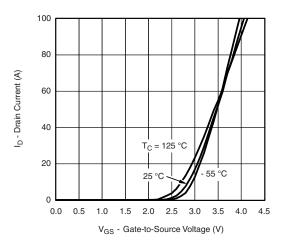


Output Characteristics

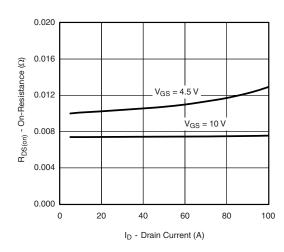


Transconductance

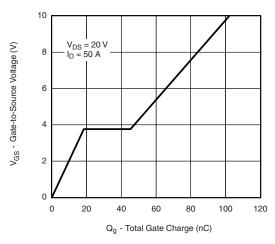




Transfer Characteristics



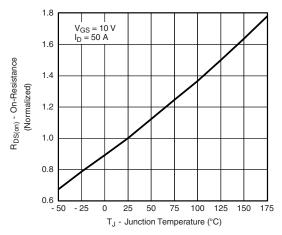
On-Resistance vs. Drain Current



Gate Charge



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

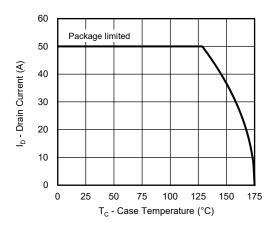


On-Resistance vs. Junction Temperature

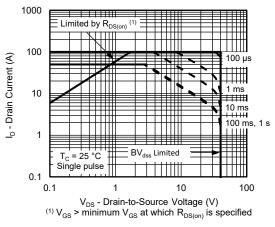
T_J = 150 °C T_J = 25 °C T_J = 25 °C V_{SD} - Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage

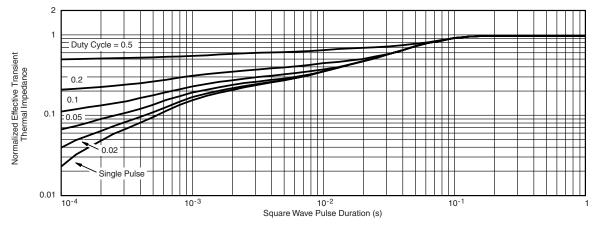
THERMAL RATINGS



Max. Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



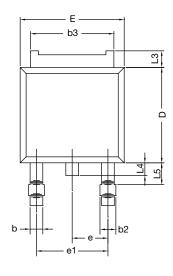
Normalized Thermal Transient Impedance, Junction-to-Case

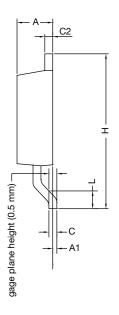
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for silicon technology and package reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg272243.



TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y







	MILLIMETERS			
DIM.	MIN.	MAX.		
Α	2.18	2.38		
A1	-	0.127		
b	0.64	0.88		
b2	0.76	1.14		
b3	4.95	5.46		
С	0.46	0.61		
C2	0.46	0.89		
D	5.97	6.22		
D1	4.10	-		
Е	6.35	6.73		
E1	4.32	-		
Н	9.40	10.41		
е	2.28	BSC		
e1	4.56	4.56 BSC		
L	1.40	1.78		
L3	0.89	1.27		
L4	-	1.02		
L5	1.01	1.52		

Note

• Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	2.18	2.39	
A1	-	0.13	
b	0.65	0.89	
b1	0.64	0.79	
b2	0.76	1.13	
b3	4.95	5.46	
С	0.46	0.61	
c1	0.41	0.56	
c2	0.46	0.60	
D	5.97	6.22	
D1	5.21	=	
Е	6.35	6.73	
E1	4.32	=	
е	2.29 BSC		
Н	9.94	10.34	

	MILLIMETERS		
DIM.	MIN.	MAX.	
L	1.50	1.78	
L1	2.74	ref.	
L2	0.51 BSC		
L3	0.89	1.27	
L4	-	1.02	
L5	1.14	1.49	
L6	0.65	0.85	
θ	0°	10°	
θ1	0°	15°	
θ2	25°	35°	

Notes

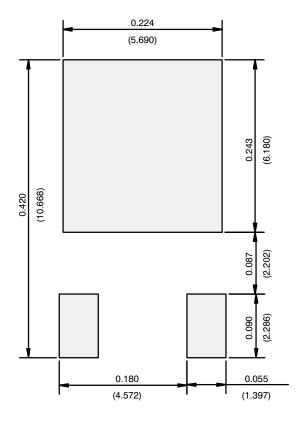
- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022

DWG: 5347



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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